

Please replace the current Abstract in the file with the following Abstract of the Disclosure:

**ABSTRACT OF THE DISCLOSURE**

A solid-state imaging element contains a plurality of photoelectric converting regions, vertical transfer portions, a horizontal transfer portion, and an output portion. These photoelectric converting regions are arranged on a surface of a semiconductor substrate along a row direction, and a column direction perpendicular to the row direction. The photoelectric converting regions are subdivided into main regions “m” having relatively wide light-receiving areas, and sub-regions “s” having relatively narrow light-receiving areas. These main areas “m” and sub-areas “s” produce signal electron charges corresponding to light having predetermined spectral sensitivities, and then store the produced signal electron charges. A partial photoelectric converting region within the photoelectric converting regions corresponds to different color light with respect to the main region “m” and the sub-region “s.”